

제23회 한국반도체학술대회

2016년 2월 22일(월)-24일(수), 강원도 하이원리조트

E. Compound Semiconductors 분과

Room K

청옥Ⅱ+Ⅲ(6층)

2016년 2월 24일(수) 10:10-11:40

[WK2-E] III-V Device

좌장 : 민병규(한국전자통신연구원), 김해천(한국전자통신연구원)

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| WK2-E-1 | 10:10-10:25 | High Performance In_{0.7}Ga_{0.3}As MOSFETs with Al₂O₃/HfO₂
Seung Woo Son, Jin Su Kim, Hwal Kim, Jung Ho Park, Do-Kywn Kim, Jung-Hee Lee, and Dae-Hyun Kim
<i>School of Electronics Engineering, Kyungpook National University</i> |
| WK2-E-2 | 10:25-10:40 | Oxidation Study on The (100), (110) and (111) Surfaces of InAs by ab-initio Calculations
In Won Yeu ^{1,2} , Cheol Seong Hwang ^{2,3} , and Jung-Hae Choi ¹
<i>¹Center for Electronic Materials, Korea Institute of Science and Technology, ²Department of Materials Science and Engineering, Seoul National University, ³Inter-University Semiconductor Research Center, Seoul National University</i> |
| WK2-E-3 | 10:40-10:55 | Improvement of Thermal Stability of Ni-InGaAs on Source and Drain by Using Pd Interlayer for High Performance N-InGaAs MOSFET
Meng Li ¹ , Jeyoung Kim ¹ , Jungwoo Oh ² , and Hi-Deok Lee ¹
<i>¹Department of Electronics Engineering, Chungnam National University, ²School of Integrated Technology, Yonsei University</i> |
| WK2-E-4 | 10:55-11:10 | Universal Mobility Behavior in In_{0.7}Ga_{0.3}As QW-MOSFETs
Jung Ho Park, Hwal Kim, Do-Kywn Kim, Jin Su Kim, Seung Woo Son, Jung-Hee Lee, and Dae-Hyun Kim
<i>School of Electronics Engineering, Kyungpook National University</i> |
| WK2-E-5 | 11:10-11:25 | The Fabrication of InGaAs MOSFET with Y₂O₃ Gate Insulator
Seong Kwang Kim ^{1,2} , Dae-Myeong Geum ^{2,3} , Jungmin Lee ¹ , Min-Su Park ² , Jae-Phil Shim ² , Chang Zoo Kim ⁴ , Hyung-jun Kim ² , Jin-Dong Song ² , Won Jun Choi ² , Sung-Jin Choi ¹ , Dae Hwan Kim ¹ , SangHyeon Kim ² , and Dong Myong Kim ¹
<i>¹School of Electrical Engineering, Kookmin University, ²Korea Institute of Science and Technology, ³Department of Materials Science and Engineering, Seoul National University, ⁴Korea Advanced Nano Fab Center</i> |
| WK2-E-6 | 11:25-11:40 | Improvement of Interfacial-state Density (D_{it}) in High-k/In_{0.53}Ga_{0.47}As MOSCAPs by D₂ High-Pressure Annealing (HPA)
Jin Su Kim ¹ , Seung Heon Shin ² , Do-Kywn Kim ¹ , Young Dae Cho ³ , Chan-Soo Shin ³ , Won-Kyu Park ³ , Manny Rivera ⁴ , Jae Ik Lew ⁴ , Jung- |

The 23rd Korean Conference on Semiconductors (KCS 2016)

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Hee Lee¹, S. K. Banergee², Tae-Woo Kim⁵, and Dae-Hyun Kim¹

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